

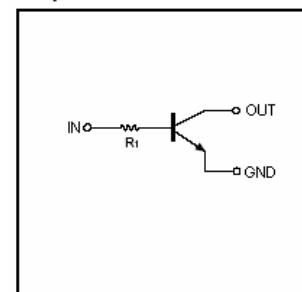


Digital transistors (built-in resistors)

DTC143TM/DTC143TE/DTC143TUA DTC143TKA /DTC143TSA/ DTC143TCA

DIGITAL TRANSISTOR (NPN)

Equivalent Circuit

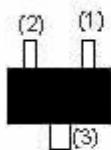


FEATURES

1. Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
2. The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
3. Only the on/off conditions need to be set for operation, making device design easy

PIN CONNECTIONS AND MARKING

DTC143TE

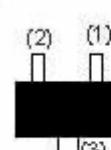


1.IN
2.GND
3.OUT

SOT-523

Addreviated symbol: 03

DTC143TUA

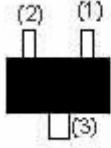


1.IN
2.GND
3.OUT

SOT-323

Addreviated symbol: 03

DTC143TKA

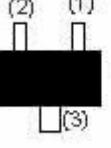


1.IN
2.GND
3.OUT

SOT-23-3L

Addreviated symbol: 03

DTC143TCA

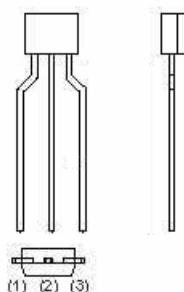


1.IN
2.GND
3.OUT

SOT-23

Addreviated symbol: 03

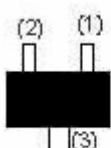
DTC143TSA



1.GND
2.OUT
3.IN

TO-92S

DTC143TM



1.IN
2.GND
3.OUT

SOT-723

Addreviated symbol: 03

Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits (DTC143T□)						Unit			
		M	E	UA	CA	KA	SA				
Collector-base voltage	$V_{(BR)CBO}$	50						V			
Collector-emitter voltage	$V_{(BR)CEO}$	50						V			
Emitter-base voltage	$V_{(BR)EBO}$	5						V			
Collector current	I_C	100						mA			
Collector Power dissipation	P_C	100	150	200		300	mW <td data-kind="ghost"></td>				
Junction temperature	T_j	150						°C			
Storage temperature	T_{stg}	-55~150						°C			

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	50			V	$I_C=50\mu A$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	50			V	$I_C=1mA$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5			V	$I_E=50\mu A$
Collector cut-off current	I_{CBO}			0.5	μA	$V_{CB}=50V$
Emitter cut-off current	I_{EBO}			0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$			0.3	V	$I_C=5mA, I_B=0.25mA$
DC current transfer ratio	h_{FE}	100		600		$V_{CE}=5V, I_C=1mA$
Input resistance	R_I	3.29	4.7	6.11	$K\Omega$	
Transition frequency	f_T		250		MHz	$V_O=10V, I_O=5mA, f=100MHz$